
2SB1103

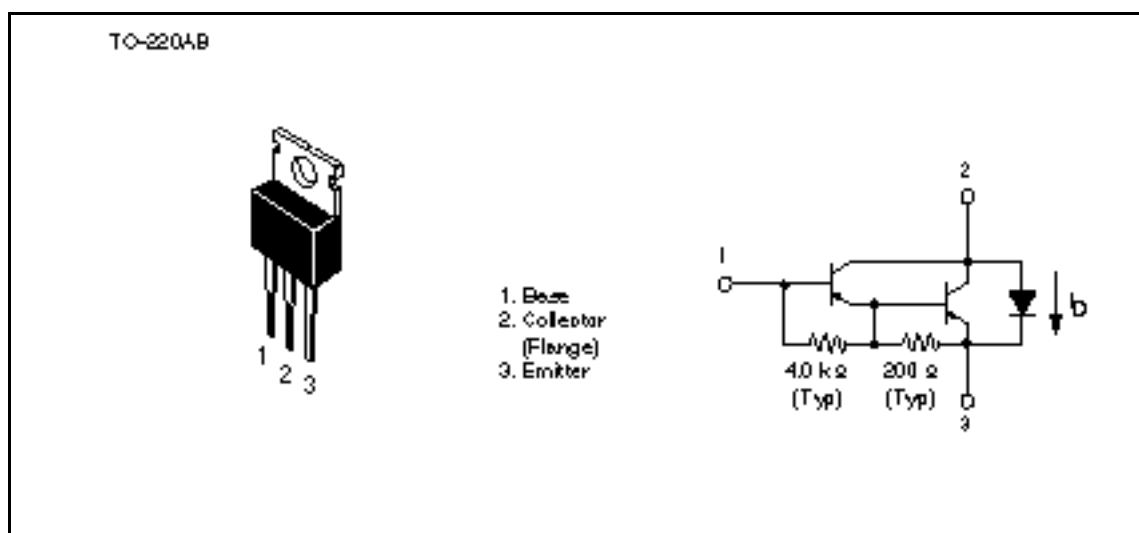
Silicon PNP Triple Diffused

HITACHI

Application

Low frequency power amplifier

Outline



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to emitter voltage	V _{CBO}	-60	V
Collector to emitter voltage	V _{CEO}	-60	V
Emitter to base voltage	V _{EBO}	-7	V
Collector current	I _C	-8	A
Collector peak current	I _{C(peak)}	-12	A
Collector power dissipation	P _C ^{*1}	40	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C
C to E diode forward current	I _D ^{*1}	8	A

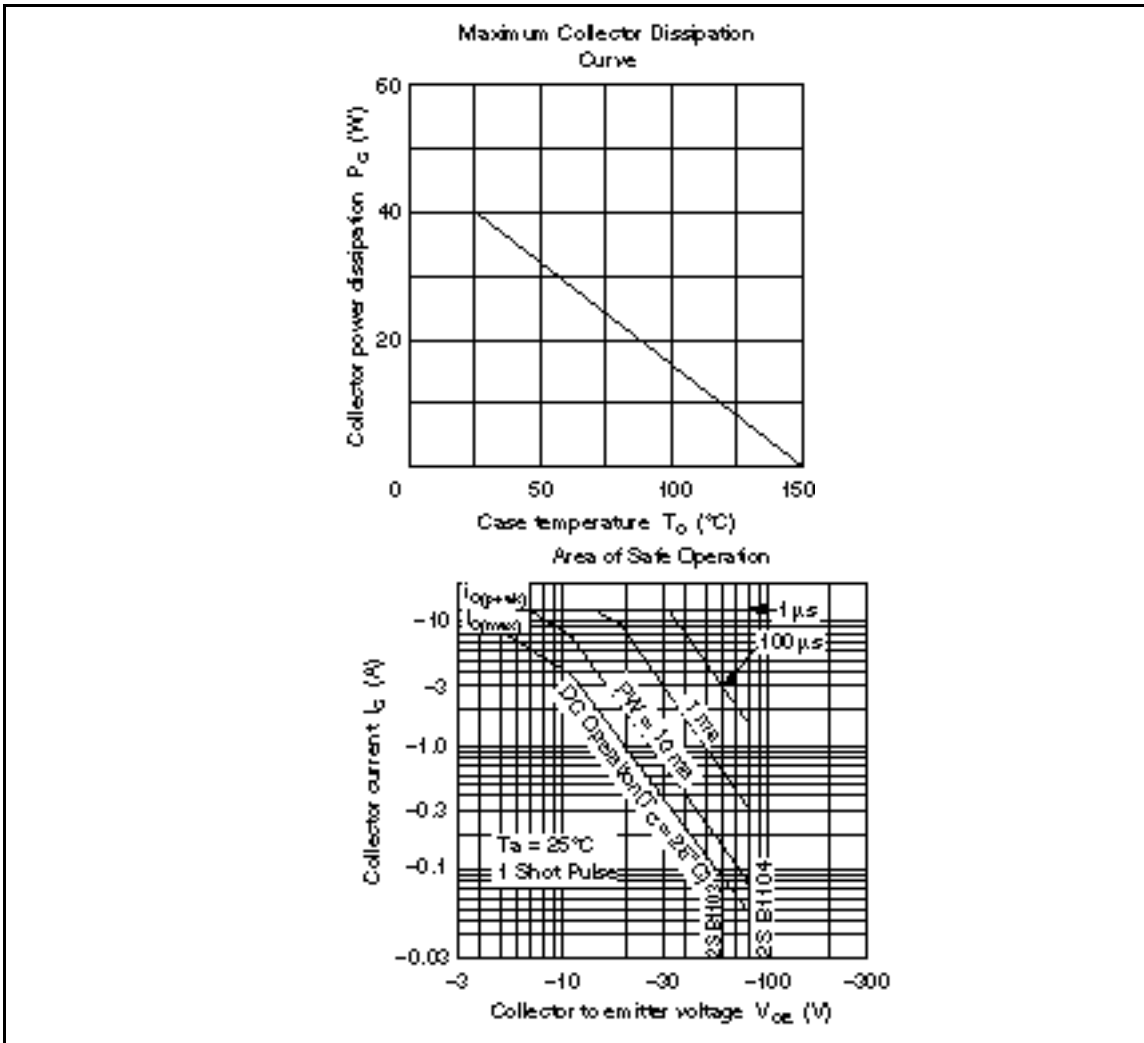
Note: 1. Value at T_C = 25°C.

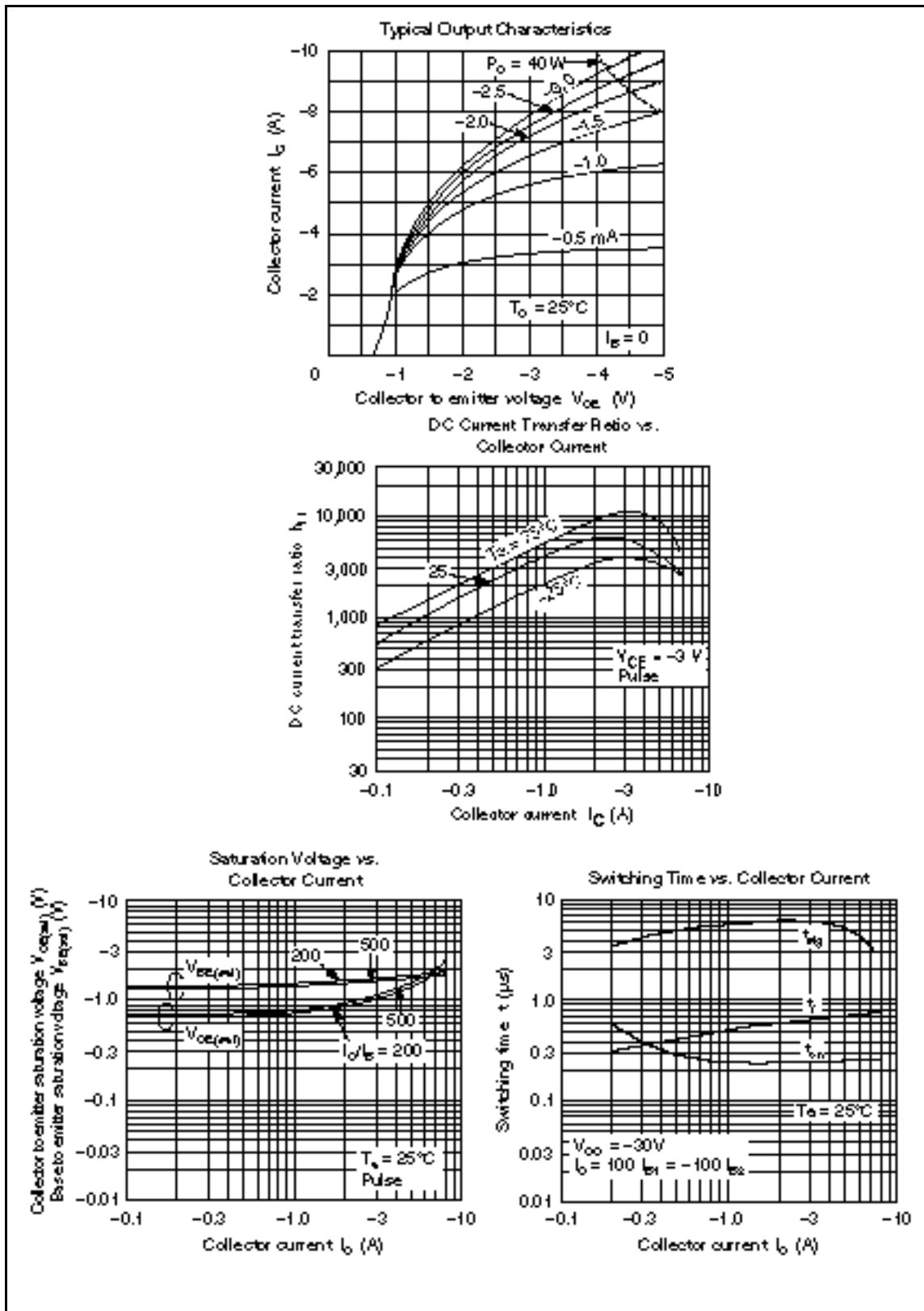
2SB1103

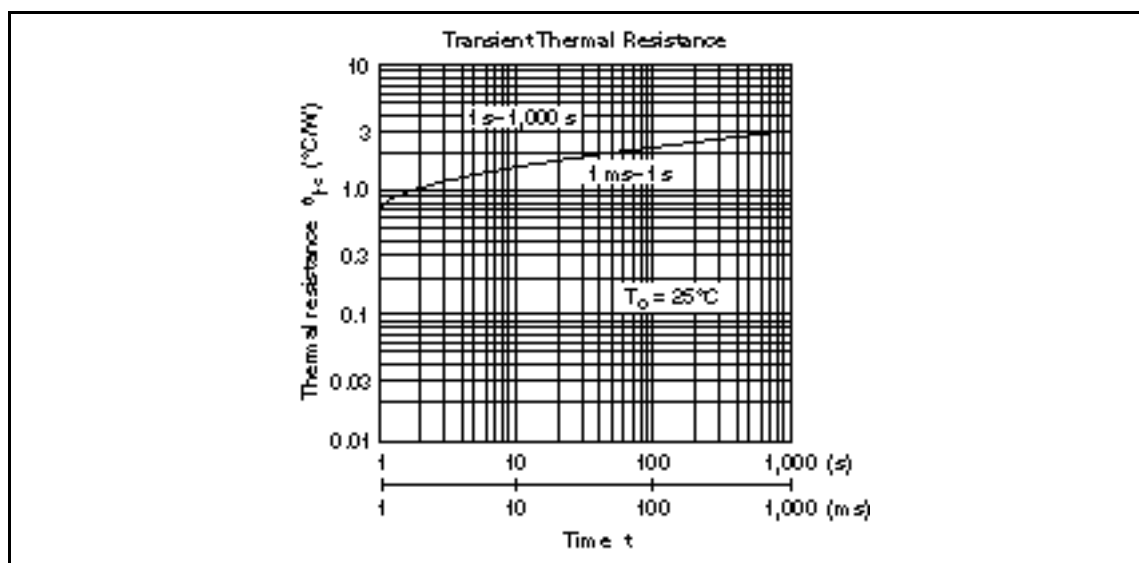
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-60	—	—	V	$I_C = -25 \text{ mA}$, $R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-7	—	—	V	$I_E = -50 \text{ mA}$, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-100	μA	$V_{CB} = -60 \text{ V}$, $I_E = 0$
	I_{CEO}	—	—	-10	μA	$V_{CE} = -50 \text{ V}$, $R_{BE} =$
DC current transfer ratio	h_{FE}	1000	—	20000		$V_{CE} = -3 \text{ V}$, $I_C = -4 \text{ A}^{*1}$
Collector to emitter saturation voltage	$V_{CE(sat)1}$	—	—	-1.5	V	$I_C = -4 \text{ A}$, $I_B = -8 \text{ mA}^{*1}$
	$V_{CE(sat)2}$	—	—	-3.0		$I_C = -8 \text{ A}$, $I_B = -80 \text{ mA}^{*1}$
Base to emitter saturation voltage	$V_{BE(sat)1}$	—	—	-2.0	V	$I_C = -4 \text{ A}$, $I_B = -8 \text{ mA}^{*1}$
	$V_{BE(sat)2}$	—	—	-3.5		$I_C = -8 \text{ A}$, $I_B = -80 \text{ mA}^{*1}$
C to E diode forward voltage	V_D	—	—	3.0	V	$I_D = 8 \text{ A}^{*1}$
Turn on time	t_{on}	—	0.5	—	μs	$I_C = -4 \text{ A}$,
Storage time	t_{stg}	—	3.0	—		$I_{B1} = -I_{B2} = -8 \text{ mA}$
Fall time	t_f	—	1.0	—		

Note: 1. Pulse Test.







When using this document, keep the following in mind:

1. This document may, wholly or partially, be subject to change without notice.
2. All rights are reserved: No one is permitted to reproduce or duplicate, in any form, the whole or part of this document without Hitachi's permission.
3. Hitachi will not be held responsible for any damage to the user that may result from accidents or any other reasons during operation of the user's unit according to this document.
4. Circuitry and other examples described herein are meant merely to indicate the characteristics and performance of Hitachi's semiconductor products. Hitachi assumes no responsibility for any intellectual property claims or other problems that may result from applications based on the examples described herein.
5. No license is granted by implication or otherwise under any patents or other rights of any third party or Hitachi, Ltd.
6. **MEDICAL APPLICATIONS:** Hitachi's products are not authorized for use in **MEDICAL APPLICATIONS** without the written consent of the appropriate officer of Hitachi's sales company. Such use includes, but is not limited to, use in life support systems. Buyers of Hitachi's products are requested to notify the relevant Hitachi sales offices when planning to use the products in **MEDICAL APPLICATIONS**.

HITACHI

Hitachi, Ltd.

Semiconductor & IC Div.
Nippon Bldg., 2-5-2, Ohite-machi, Chiyoda-ku, Tokyo 100, Japan
Tel: Tokyo (03) 3270-2111
Fax: (03) 3270-5109

For further information write to:

Hitachi America, Ltd.
Semiconductor & IC Div.
2000 Sierra Point Parkway
Brisbane, CA 94005-4835
U.S.A.
Tel: 415-589-8300
Fax: 415-589-4207

Hitachi Europe GmbH
Electronic Components Group
Continental Europe
Dornacher StraÙe 3
D-85622 Feldkirchen
München
Tel: 089-9 91 80-0
Fax: 089-9 29 30 00

Hitachi Europe Ltd.
Electronic Components Div.
Northern Europe Headquarters
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 6YA
United Kingdom
Tel: 0628-885000
Fax: 0628-778322

Hitachi Asia Pte. Ltd.
45 Collyer Quay #20-00
Hitachi Tower
Singapore 0404
Tel: 535-2100
Fax: 535-1533

Hitachi Asia (Hong Kong) Ltd.
Unit 705, North Tower,
World Finance Centre
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon
Hong Kong
Tel: 27359218
Fax: 27308074